

Cost Effective ToF Lidar Using GaN Devices

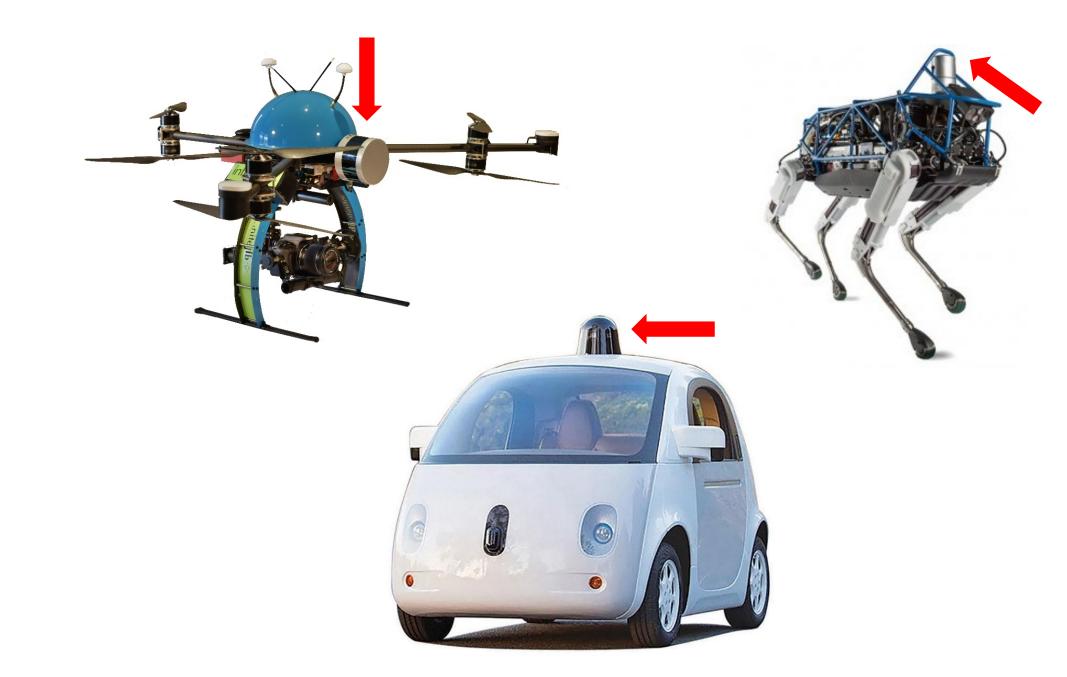
John Glaser Alex Lidow



Topics

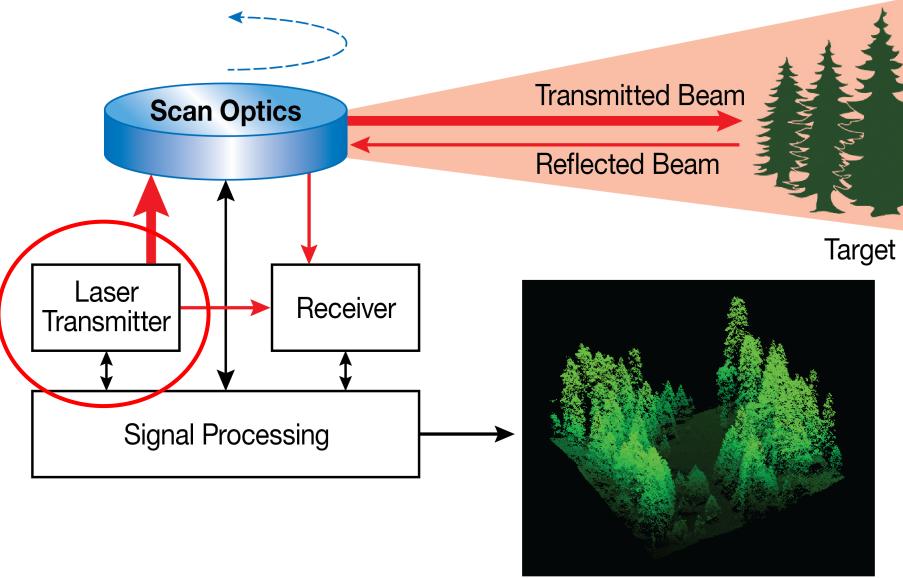
- What is lidar?
- Basic lidar laser drivers
- Why eGaN® FETs?
- Inductance
- Layout
- Performance examples
- Conclusion Upcoming trends

Lidar for Autonomous Vehicles





What is Lidar?



3-D Point Cloud

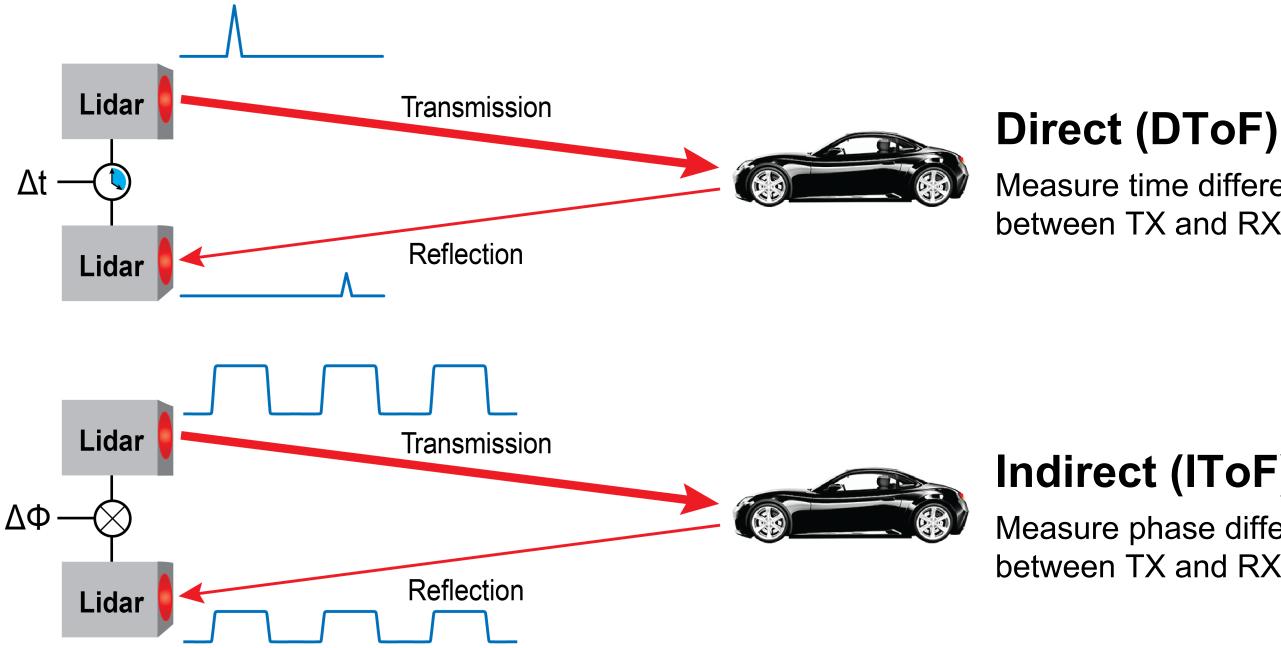


Types of Lidar

- Time of flight (ToF) for distance measurement
 - Doppler
 - Spectroscopic
 - Multispectral
 - Polarized



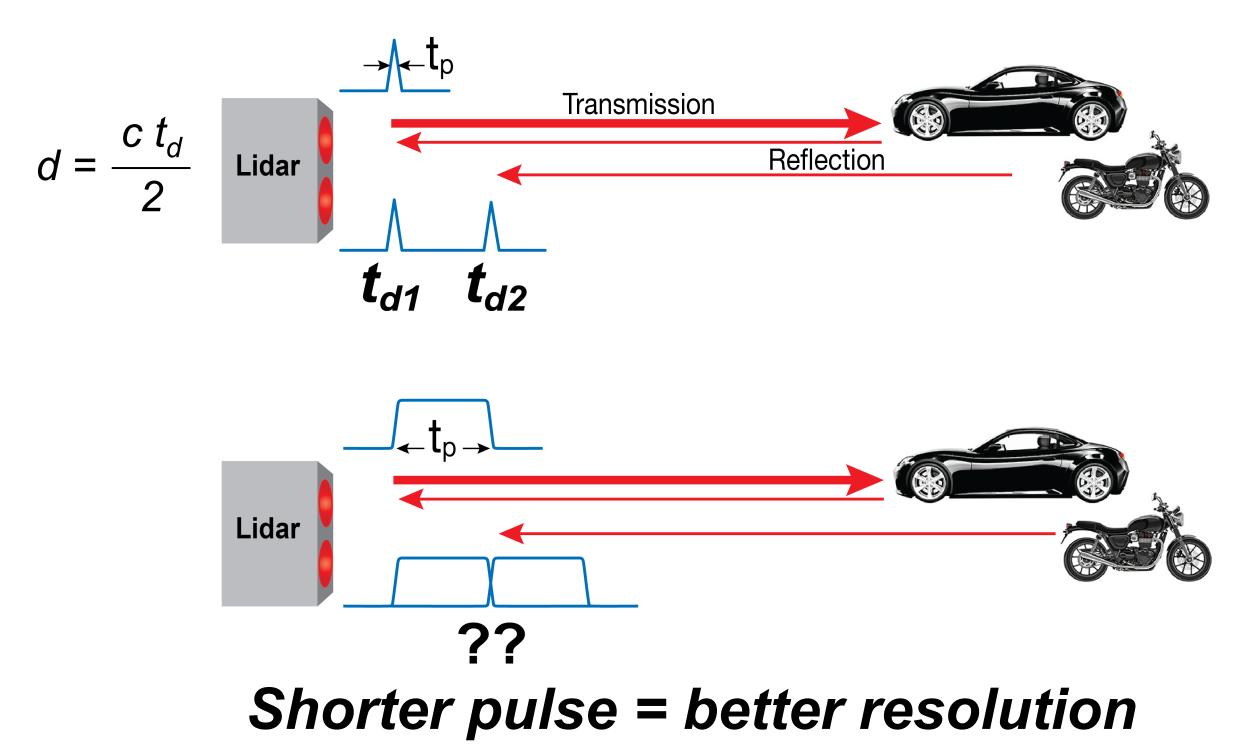
Direct vs. Indirect ToF



Measure time difference between TX and RX pulse

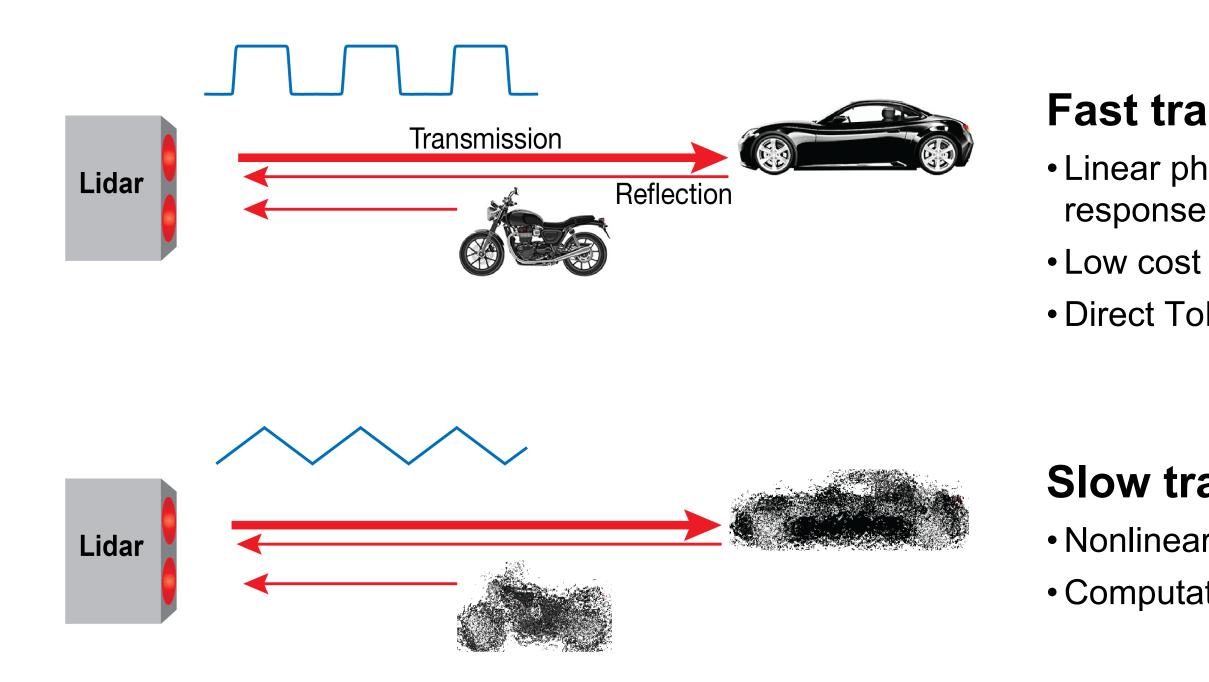
Indirect (IToF) Measure phase difference between TX and RX envelope

Importance of Pulse Shape (Direct)





Importance of Pulse Shape (Indirect)



Fast transition

- Linear phase and time
- Low cost CMOS detector
- Direct ToF readout

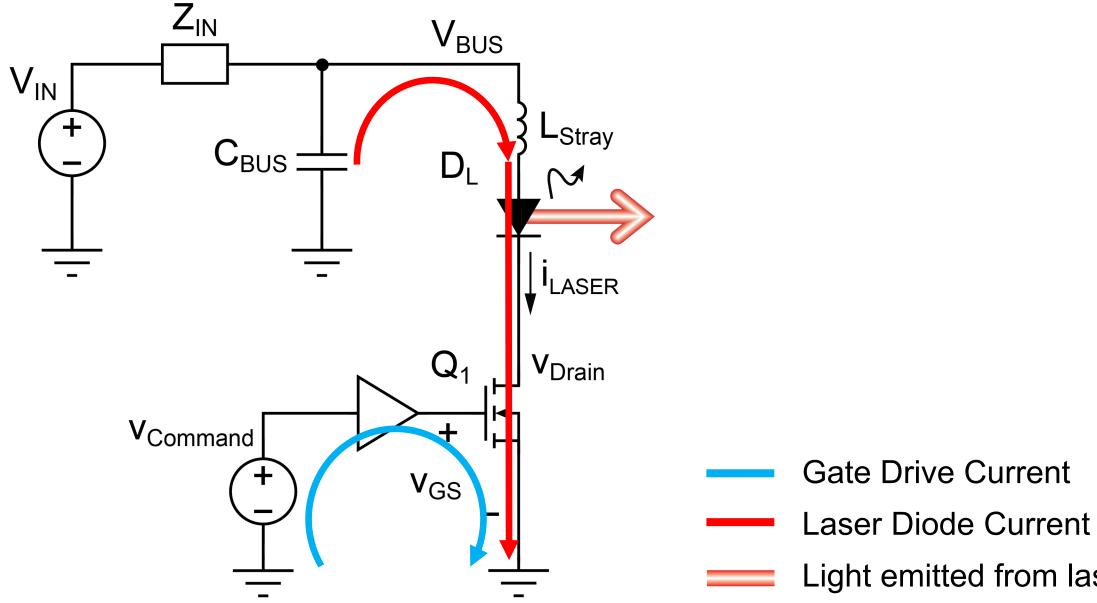
Slow transition • Nonlinear response Computation required

Amplitude (Both)

- Higher pulse amplitude = increased range
- Pulse amplitude limits:
 - Laser thermal limitations
 - Eye safety limits



Laser Transmitter Circuit



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Light emitted from laser

Pulse Width and Amplitude

Long-Range Lidar Target: Up to 300 m Pulse: 5 ns - 50 ns50 A - 500 A **Short-Range Lidar** Target: Up to 10 m Pulse: 0.5 ns - 5 ns5 A – 50 A



Why GaN?

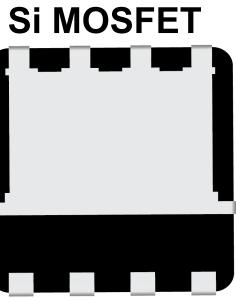
Parameter	EPC2212	Best in Class
Technology	GaN FET	Si MOSFET
V _{DS,max} (V)	100	100
$R_{DS(on)}(m\Omega)$	14	21
I _{pulse,max} (A) @ 4.5 V	75	80
Q _{Gtot} (nC)	3.2	7.6
R _{gate} (W)	0.4	1.0
$R_{gate} \bullet Q_{Gtot} (\Omega \bullet nC)$	1.3	7.6
L _{gate} (nH)	0.2	3.0
L _{source} (nH)	0.1	0.3
L _{drain} (nH)	0.1	1.0
Package (mm x mm)	LGA 2.1 x 1.6	DFN 3.3 x 3.3
AEC-Q101	YES	NO



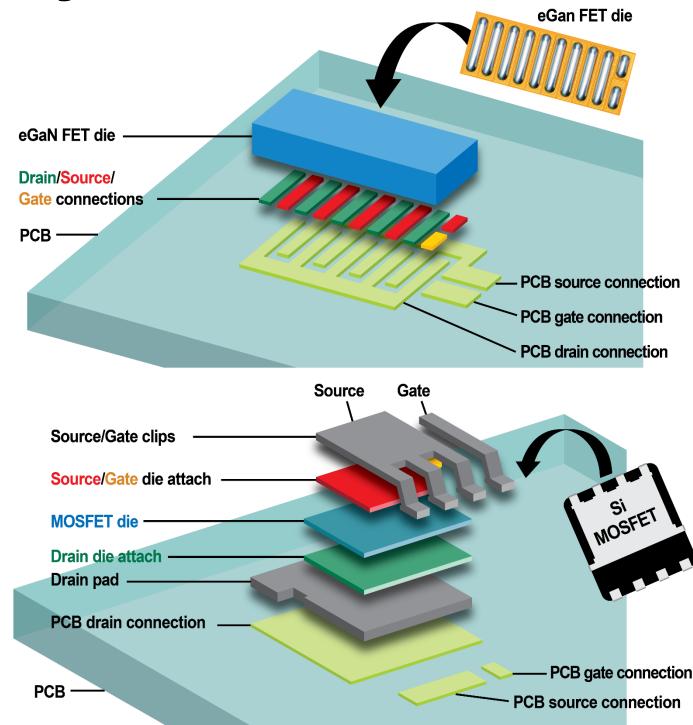








Why GaN?



Simple chip-scale package

- Low inductance
- Small size

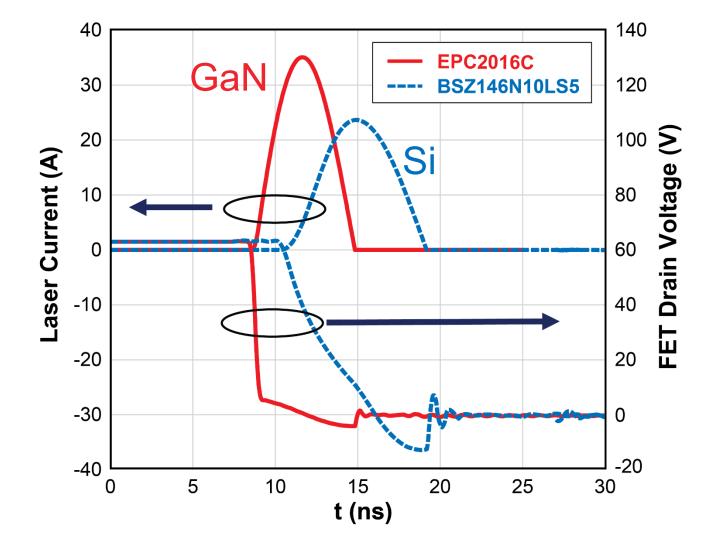
Complex package

- High inductance lacksquare
- Large size •



Simulated Performance

$$I_{DLpk}$$
 = 36 A, L_{LASER} = 3 nH, t_w = 4.0 ns \rightarrow V_{IN} = 69.0 V, C_1



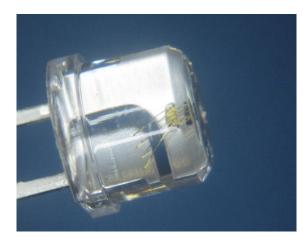
FET	Tech	I _{DLpk} (A)	t _w (ns)
Ideal Switch	Ideal	36.0	4.00
EPC2016C	GaN	35.1	4.02
Best in Class	Si	23.7	5.21

- Customer demands are for even higher current and shorter pulses
- Silicon has already hit the limit!

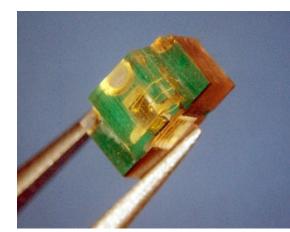
= 1.22 nF

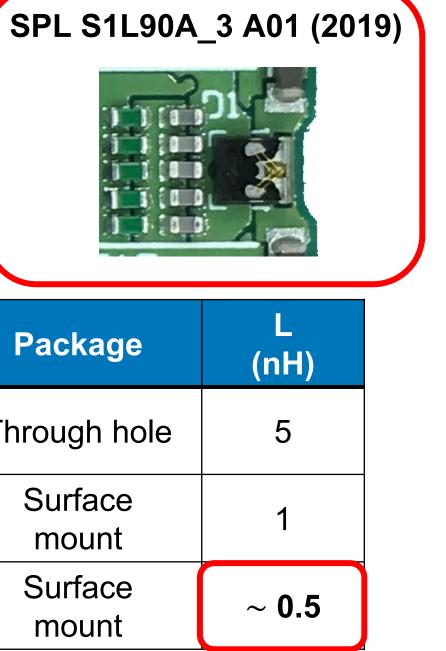
Laser Diodes

SPL PL90_3 (c. 2007)



TPGAD1S09H (c. 2013)





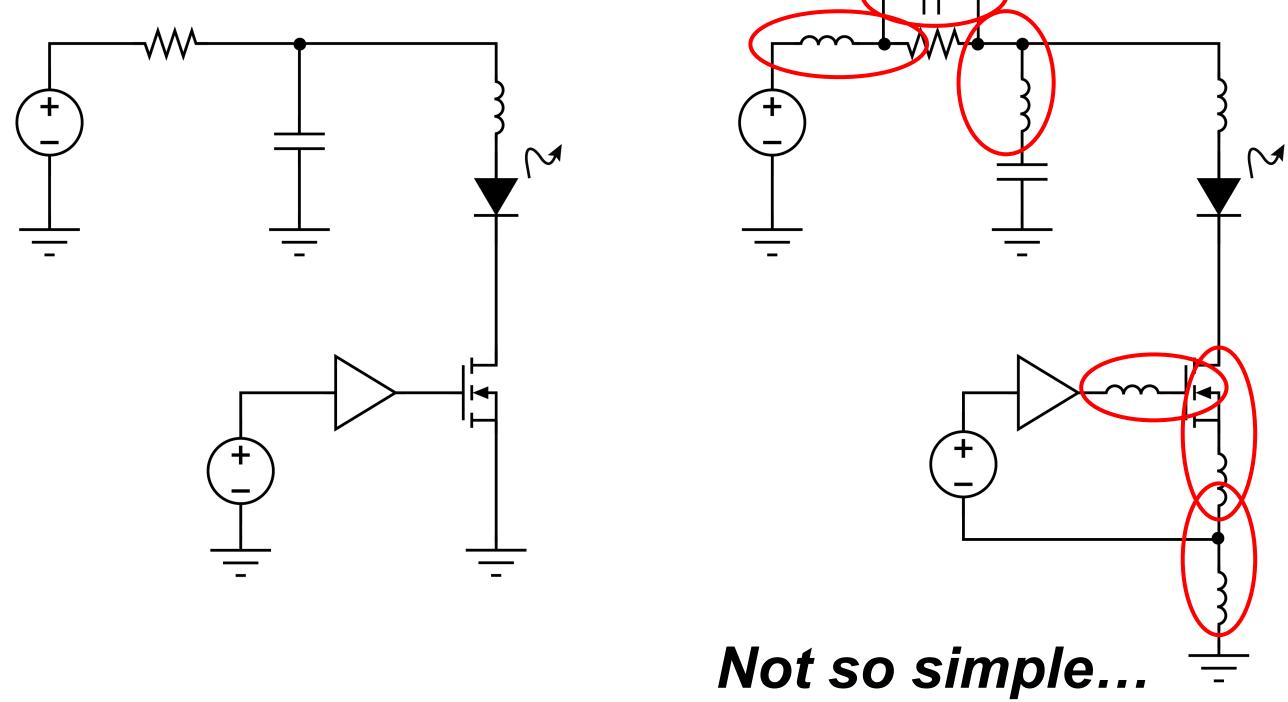
Part No.	λ (nm)	I _{Fmax} (A)	V _{Fmax} (V)	P _{opt,max} (W)	Package
SPL PL90_3	905	30	9	75	Through hole
TPGAD1S09H	905	30	12.5	75	Surface mount
SPL S1L90A_3 A01	905	40	11	125	Surface mount

Design and Layout

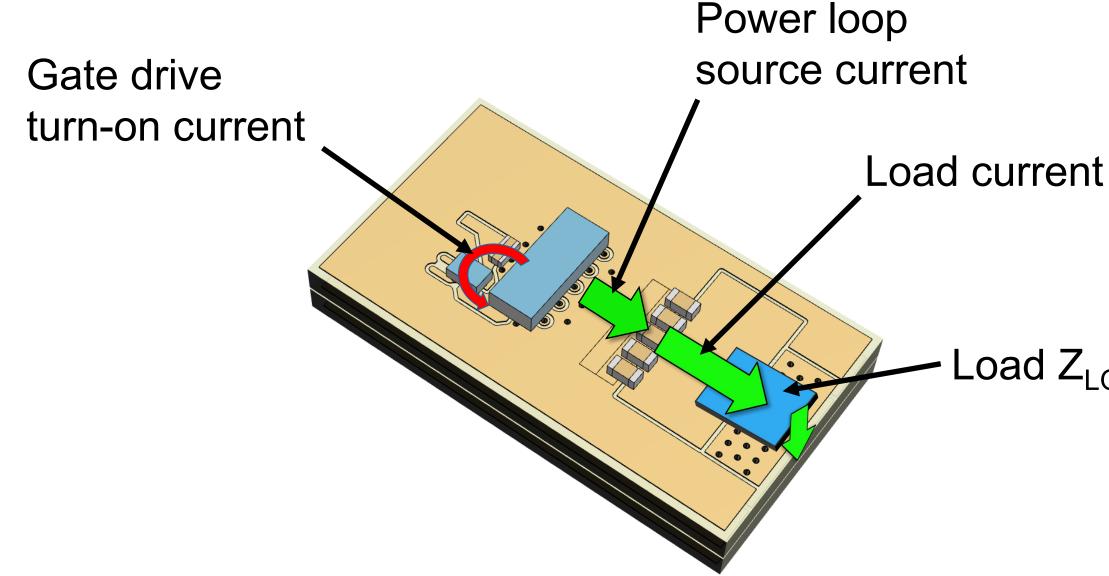
Minimize:

- Power loop inductance
- Gate loop impedance
- Mutual inductance

Simple?

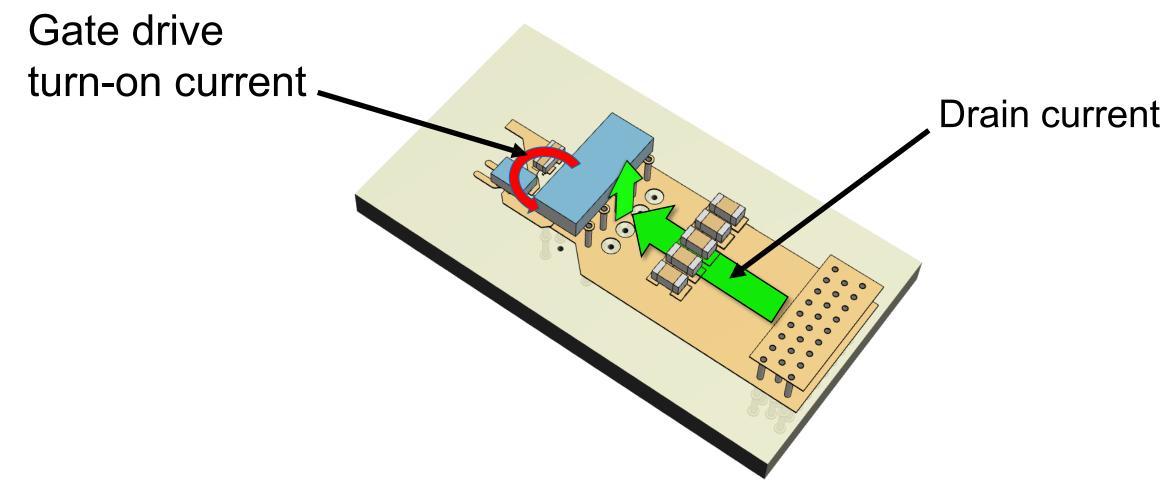


Layer 1 (top): Source Current

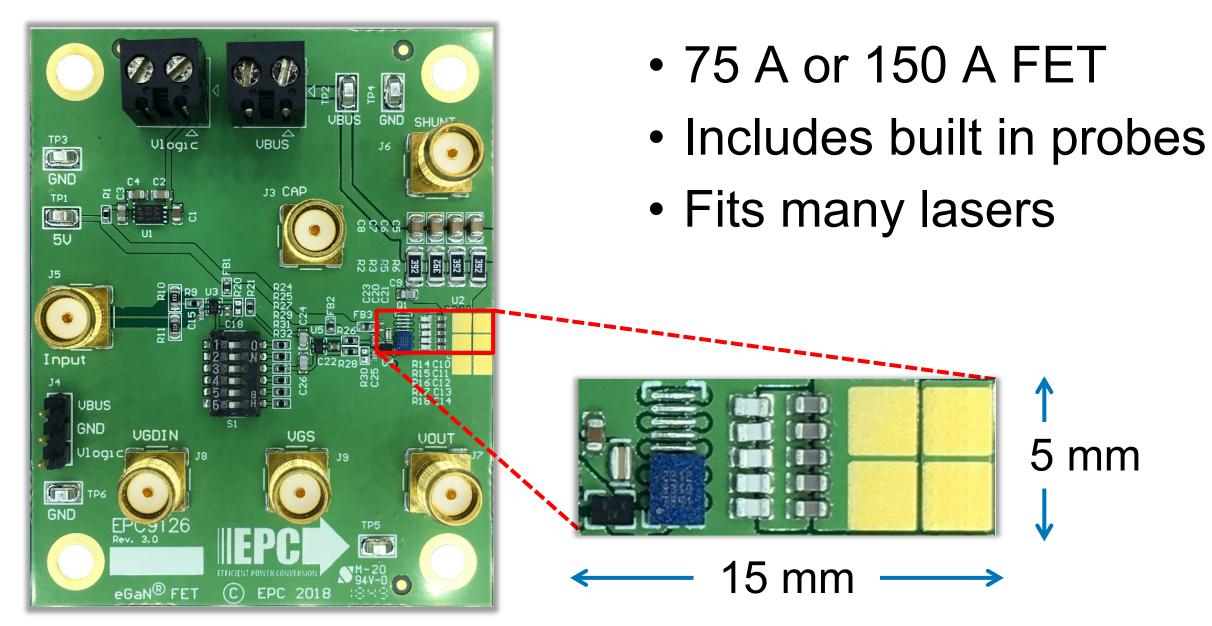


Load Z_{LOAD}

Layer 2: Drain Current

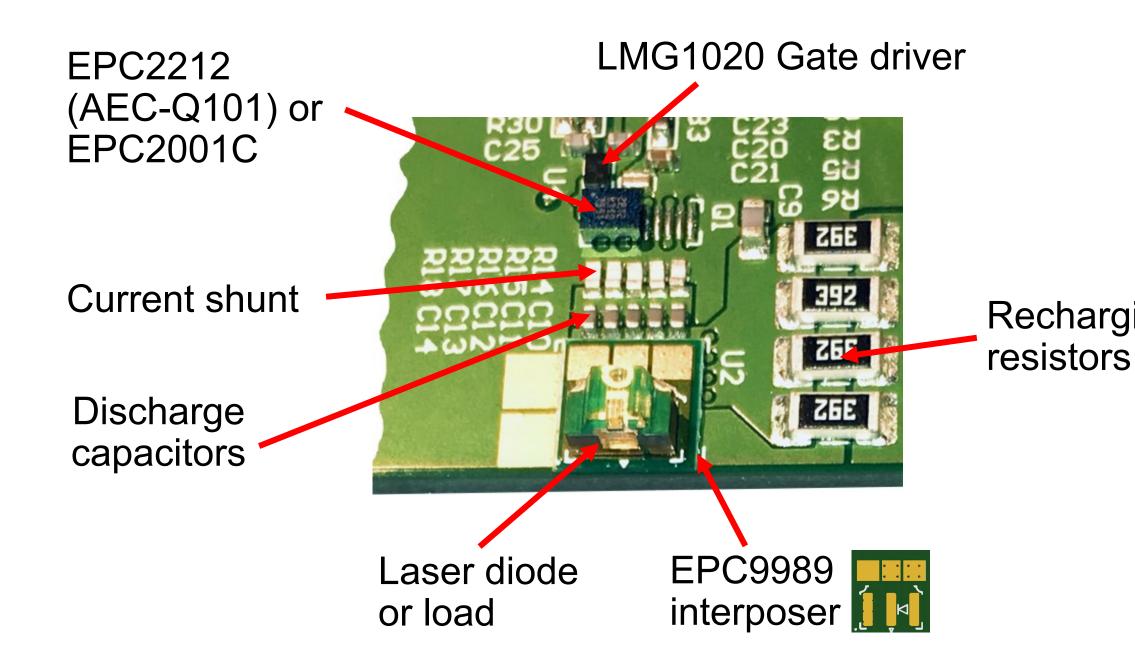


EPC9126 Laser Driver (DToF)



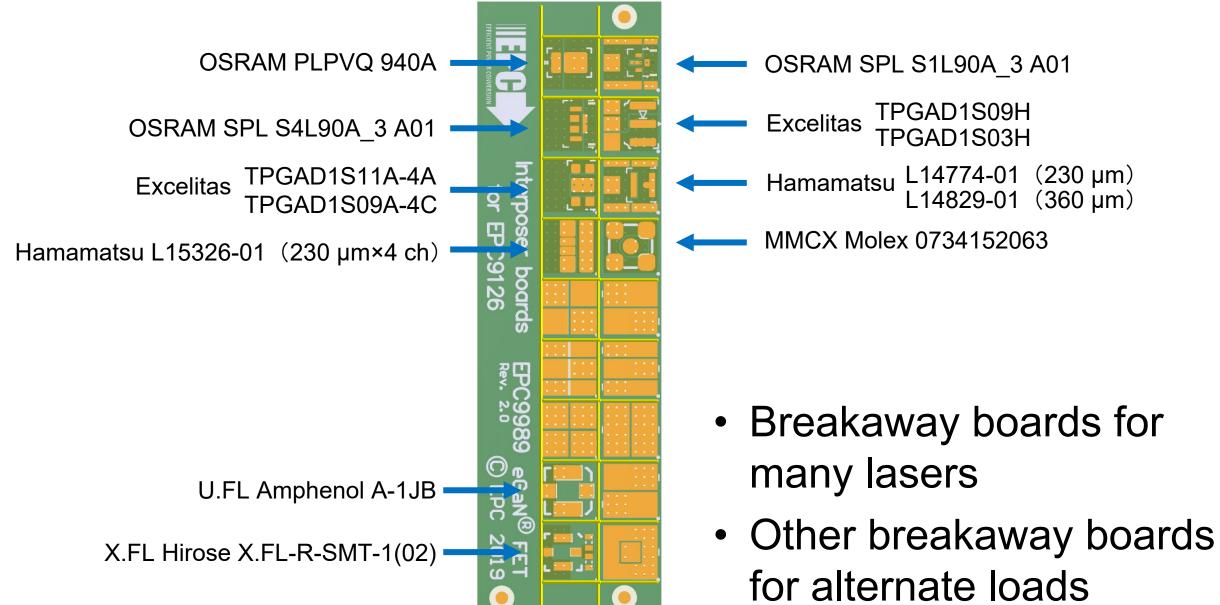


EPC9126 Laser Driver (DToF)

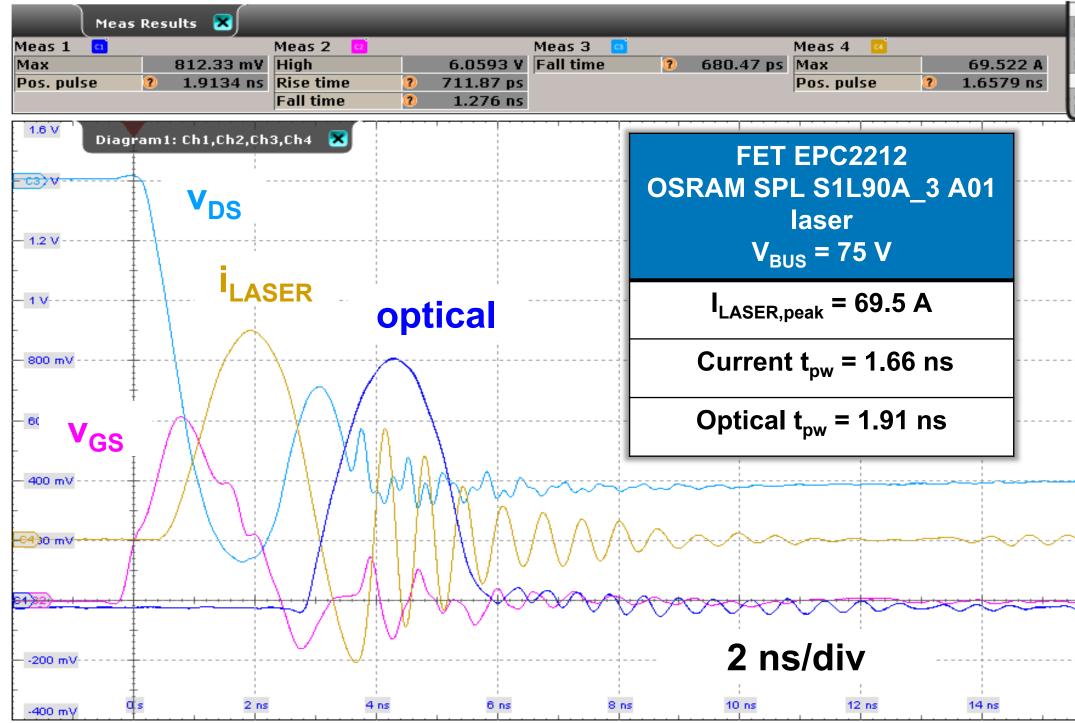


Recharging

EPC9989 Interposer

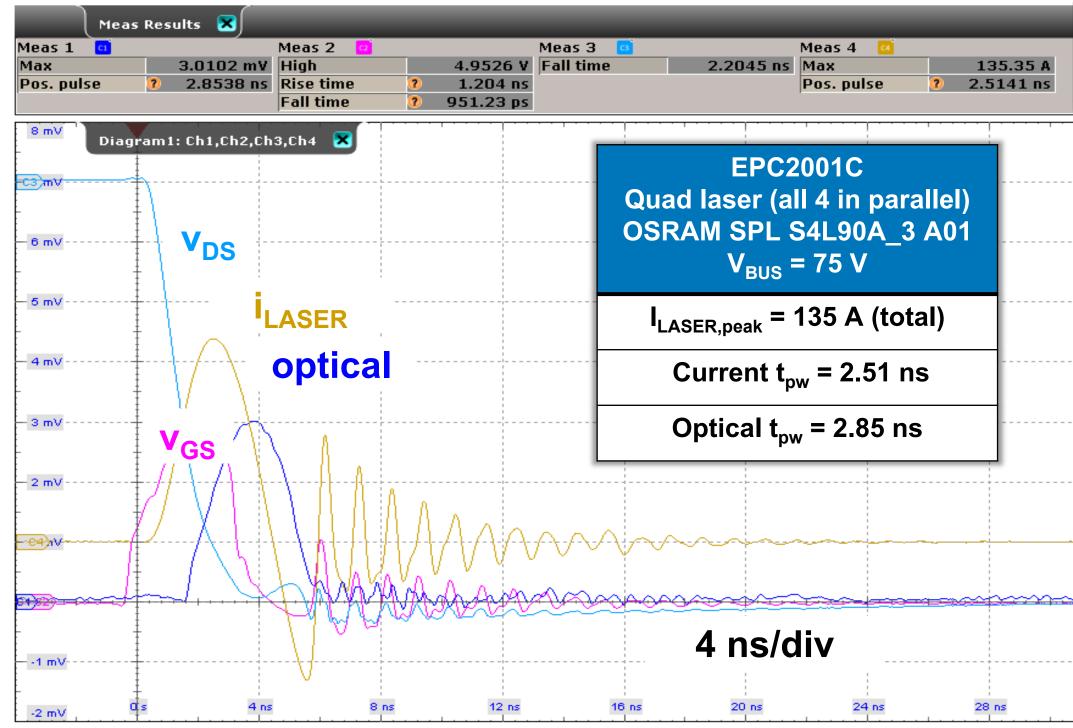


EPC9126 Rev 3 (DToF)



	•
Horizontal Res:20 ps / 10 GSa/s	5
RL: 1 kSa Scl: 2 ns/div	11
	Jto
A: Edge <mark>∡ Ch2</mark> Lvl: 1.9573 V	
	-
Ch1Wfm1 Scl: 200 mV/div	
- Pos: -3 div Off: 0 V Cpl: DC 50Ω / INV	
Cpl: DC 50Ω / INV Dec:Sa TA: Av BW: 2 GHz	
BW: 2 GHz	
Ch2Wfm1 Scl: 2 V/div	
Pos: -3 div Off: 0 V	
Cpl: DC 50Ω Dec:Sa TA: Av	
BW: 2 GHz	
Ch3Wfm1	
Scl: 10 V/div Pos: 4 div	
- Off: 0 V Cpl: DC 50Ω Dec:Sa TA: Av	
Dec:Sa TA:Av BW:2GHz	
Ch4Wfm1	
Ch4Wfm1 Scl: 20 A/div Pos: -1.98 div	1
Off: 0 A Cpl: DC 50Ω / INV	
Dec:Sa TA: Av BW: 2 GHz	
	1
\sim	-
	-
	-
16 ns 18 n:	5

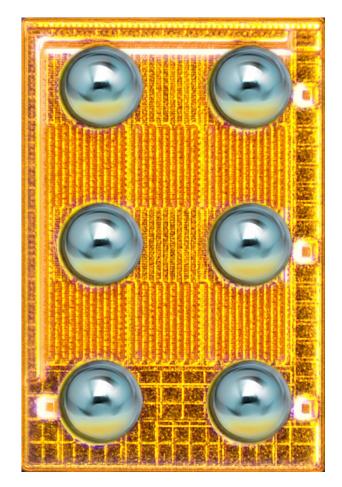
High Current EPC9126HC (DToF)



Horizontal	•
Res:40 ps / 10 GSa, RL: 1 kSa Scl: 4 ns/div Pos:0 s	IT
Trigger A A: Edge Ch2 Lvl: 2.4911 V	luto
Ch1Wfm1 Scl: 1 mV/div Pos: -3 div Off: 0 V Cpl: DC 50Ω Dec:Sa TA: Av BW: 2 GHz	
Ch2Wfm1 Scl: 2 V/div	
Pos: -3 div Off: 0 V Cpl: DC 50Ω Dec:Sa TA: Av BW: 2 GHz	
Ch3Wfm1	
Scl: 10 V/div Pos: 4 div Off: 0 V Cpl: DC 50Ω Dec:Sa TA: Av BW: 2 GHz	
Ch4Wfm1 Scl: 40 A/div	
Pos: -2 div Off: 0 A Cpl: DC 50Ω / INV Dec:Sa TA: Av BW: 2 GHz	,
32 ns 36	ns

EPC2216 for *Picosecond* Speeds

- EPC2216 eGaN[®] FET
 - 15 V, 3.4 A, 20 mΩ
 - 2 x 3 BGA
 - 870 pC gate charge
 - 28 A pulse current

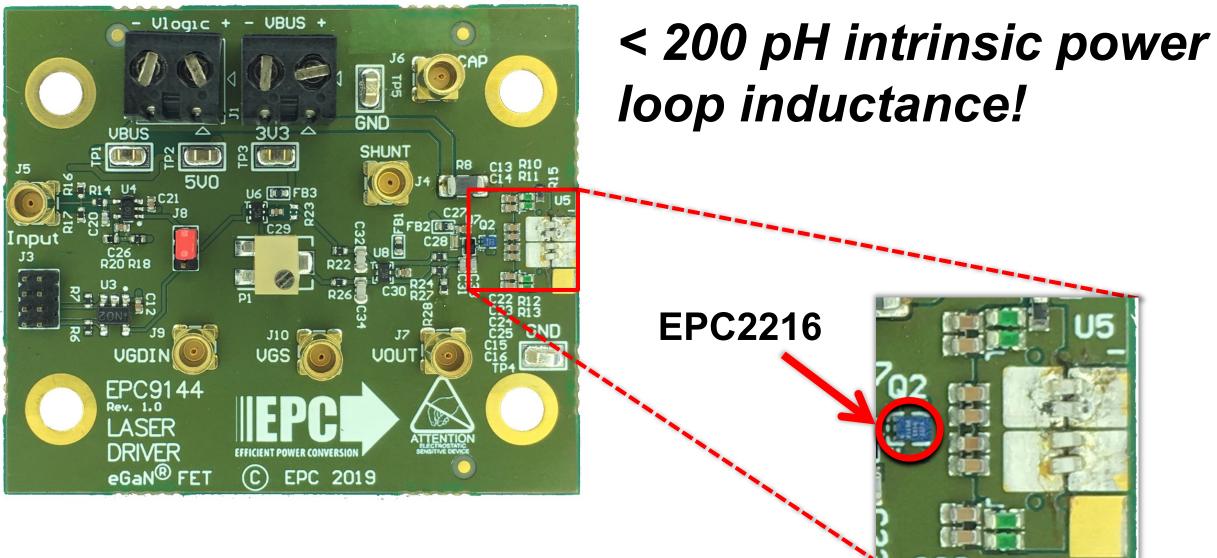


0.85 mm x 1.2 mm

AEC-Q101 Automotive Qualified!



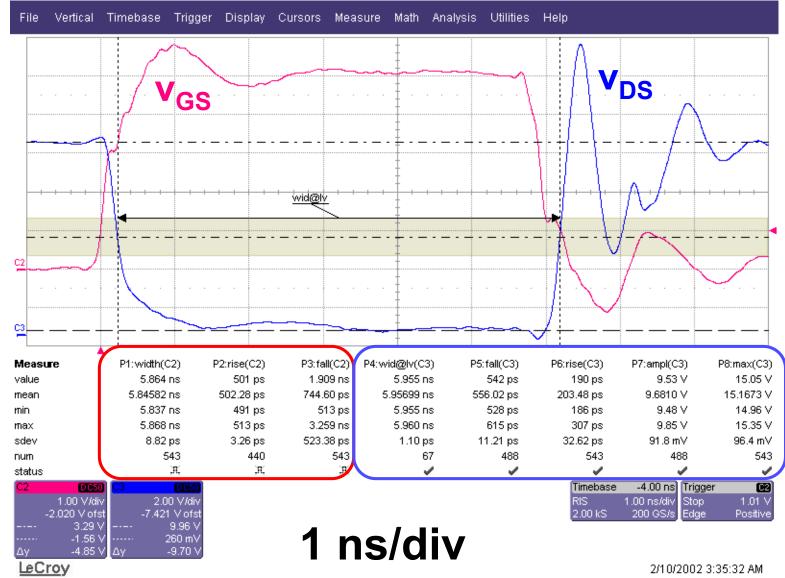
EPC9144 (IToF)



Driver stage detail

Long Pulse $V_{BUS} = 10.1 V$

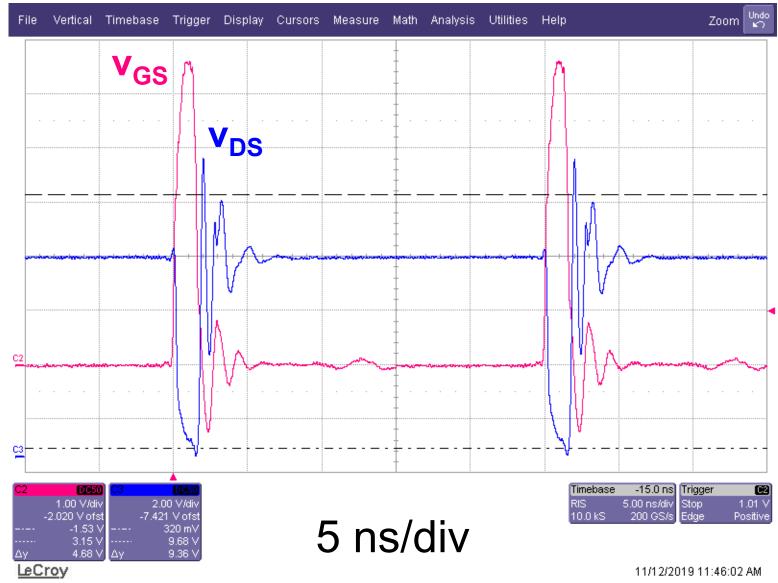
- 1 Ω resistor load
- $I_{DS,max} = 9.9 A$
- t_{on} = 556 ps
- • $t_{off} = 203 \text{ ps}$



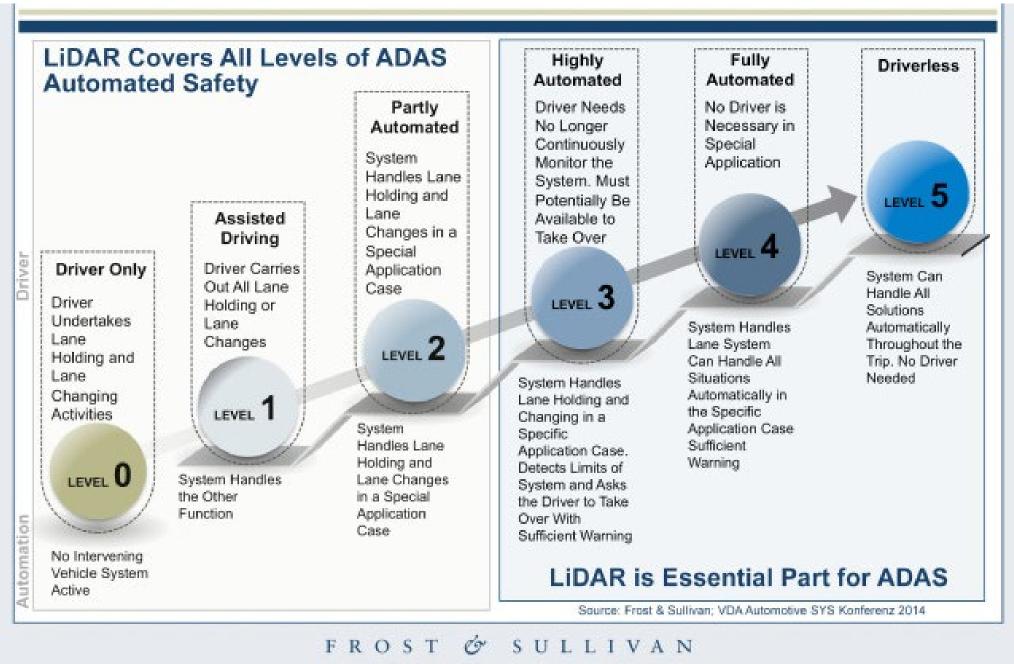
High Frequency $V_{BUS} = 7.9 V$

1 Ω resistor load

• f_{pulse} = 40 MHz



The Pathway to Self Driving Cars



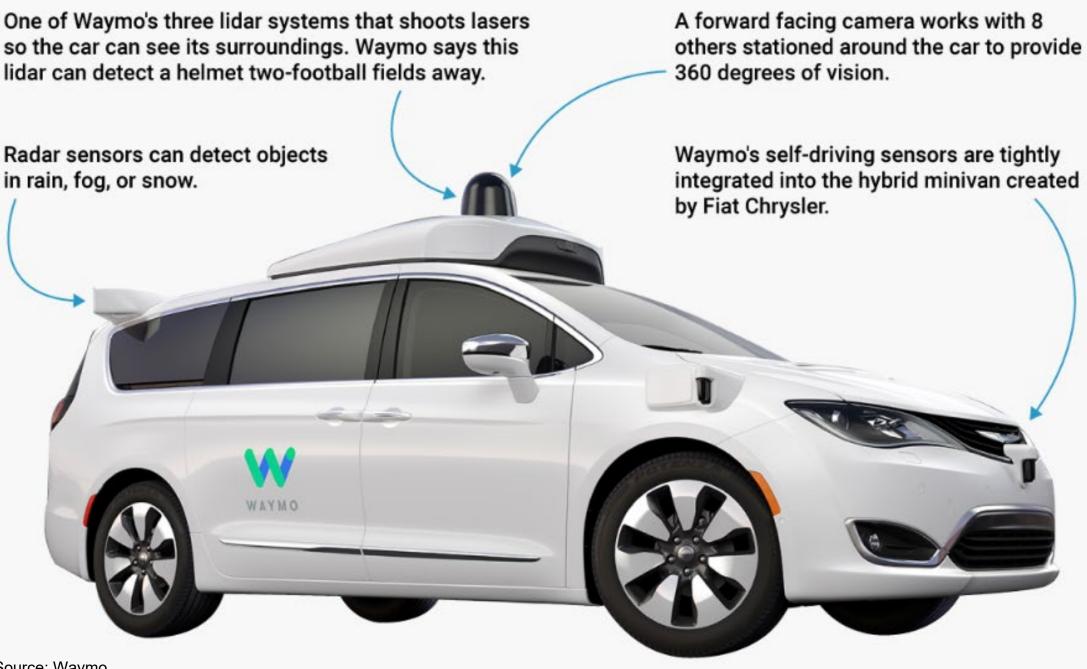
What is Required for Autonomous Cars?

300 meters (Approximately 11 seconds at 60 mph)

- Higher output lasers
 - Going to longer wavelengths (1500 nm vs 903 nm) allows for higher output power without danger to the human eye.
 - 1440 nm lasers and detectors are more expensive
 - Edge emitting LEDs are more efficient than VCSEL and have superior brightness
 - VCSEL lasers can be lower overall cost, but shorter range
- More sensitive detectors
 - Geiger mode can detect single photons but takes time to "reset".



How Waymo's Self Driving Car "Sees"



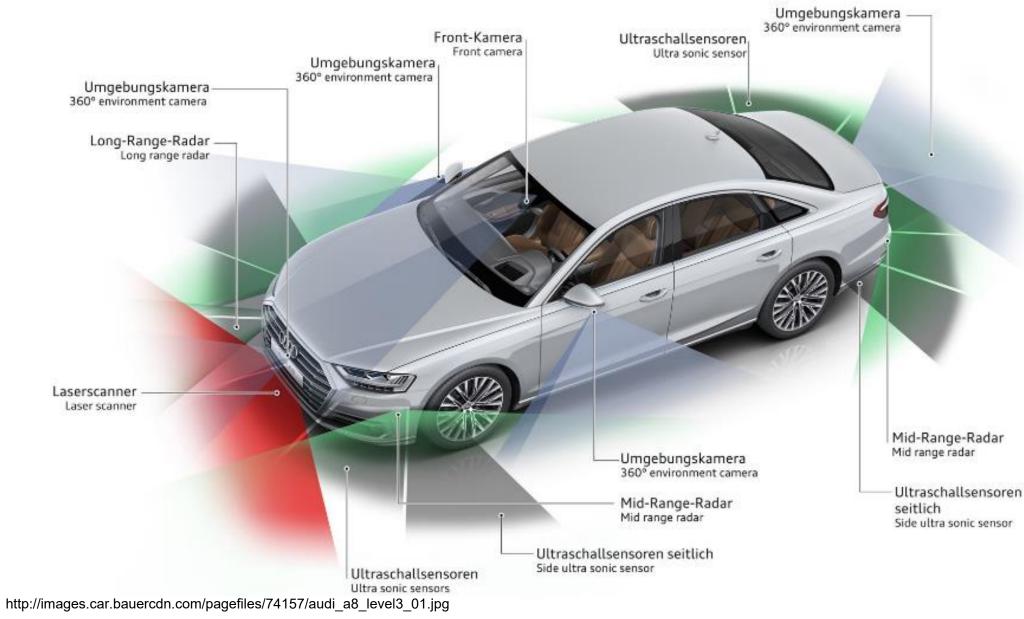
Source: Waymo







How Does Audi's ADAS A8 "See"





Lidar Myths

- Lidar can't see in fog, snow or rain.
 - Lidar can see as well as, or better than a human.
- Spinning disk Lidar is unreliable.
 - There are lots of reliable spinning disks in every car.
- Lidar is too expensive.
 - Flash Lidar is much less expensive than spinning Lidar
 - Automotive companies have a way of grinding down cost.

The Future

- Lidar will be used on all cars.
- Lidar will be about as expensive as a headlamp.
- Lidar (scanning) + Lidar (flash) + Camera will be able to handle most autonomous functions.

Upcoming Trends

- Laser arrays
- Fewer lasers in a system
- MEMS/solid-state beam steering
- Automotive uptake slow and steady
- Commercial, consumer, industrial taking off
- Huge innovation in optics and detection technology

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